





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
30V	5Ω @ V _{GS} = 4V	200mA
307	7Ω @ $V_{GS} = 2.5V$	115mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Brushless DC Motor Control
- DC-DC Converters
- Load Switch

Features

- N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

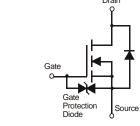
Mechanical Data

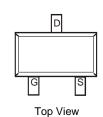
- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed Over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)





Top View





Equivalent Circuit

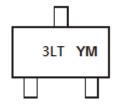
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN33D8LTQ-7	SOT523	3,000/Tape & Reel
DMN33D8LTQ-13	SOT523	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



3LT = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2018	8	2019		2020	20	21	2022		2023	2	2024
Code	F		G		Н		l	J		K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gain-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 6)	Continuous	I _D	115	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	240	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	521	°C/W
Total Power Dissipation (Note 7)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	420	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

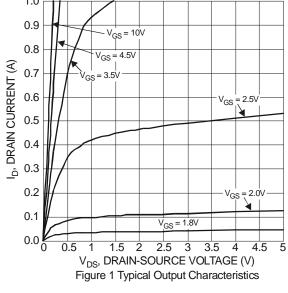
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

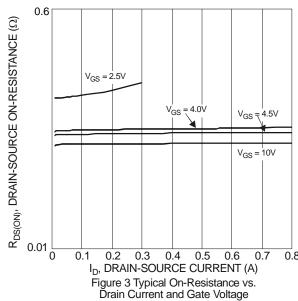
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Body Leakage	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	0.8		1.5	V	$V_{DS} = 3V, I_D = 100\mu A$		
Static Drain-Source On-Resistance	Ь	_		5	Ω	$V_{GS} = 4V$, $I_D = 10mA$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	7	Ω	$V_{GS} = 2.5V, I_D = 5mA$		
Diode Forward Voltage	V_{SD}	_		1.2	V	$V_{GS} = 0V, I_{S} = 115mA$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}	_	48			$V_{DS} = 5V, V_{GS} = 0V, f = 1.0MHz$		
Output Capacitance	Coss	_	11	_	pF			
Reverse Transfer Capacitance	C _{rss}	_	8	_				
Total Gate Charge (V _{GS} = 10V)	Qg	_	0.55	_				
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	1.23	_	nC	$V_{GS} = 10V, V_{DS} = 10V,$		
Gate-Source Charge	Q_{gs}	_	0.14	_	IIC	$I_D = 250 \text{mA}$		
Gate-Drain Charge	Q _{gd}	_	0.14	_				
Turn-On Delay Time	t _{D(ON)}	_	2.9	_				
Turn-On Rise Time	t _R		2.6	_	ns	$V_{DD} = 30V, I_D = 0.2A, V_{GEN} = 10V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	18.2	_	115	$R_{GEN} = 25\Omega$		
Turn-Off Fall Time	t _F		13.6	_				

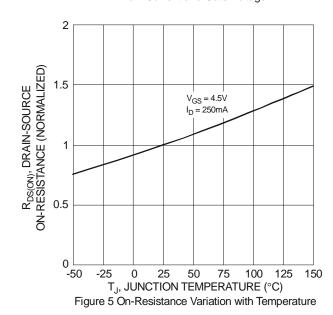
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



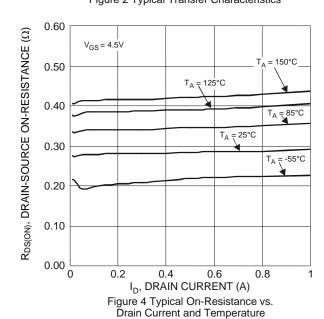








 $\begin{array}{c} 1 \\ 0.8 \\ \hline \\ 0.8 \\ \hline \\ 0.4 \\ \hline \\ 0.2 \\ \hline \\ 0.2 \\ \hline \\ \\ T_A = 150^{\circ}\text{C} \\ \hline \\ T_A = 150^{\circ}\text{C} \\ \hline \\ T_A = 25^{\circ}\text{C} \\ \hline \\ \\ T_A = 55^{\circ}\text{C} \\ \hline \\ \\ V_{GS}, \text{ GATE-SOURCE VOLTAGE (V)} \\ \hline \\ \text{Figure 2 Typical Transfer Characteristics} \end{array}$



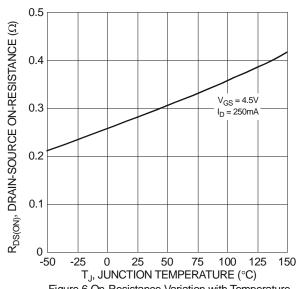


Figure 6 On-Resistance Variation with Temperature



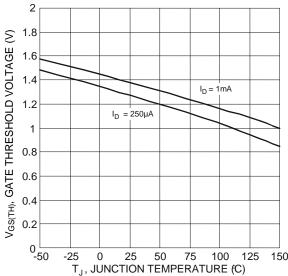
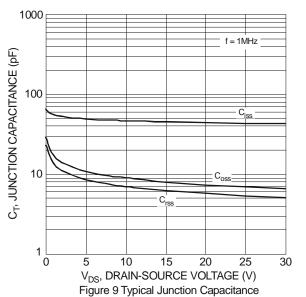
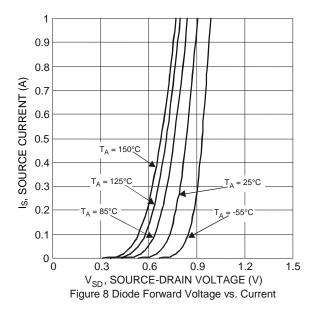
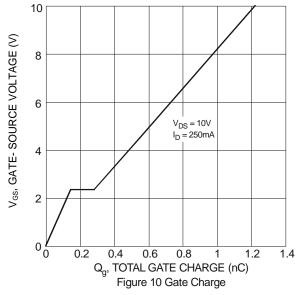


Figure 7 Gate Threshold Variation vs. Junction Temperature





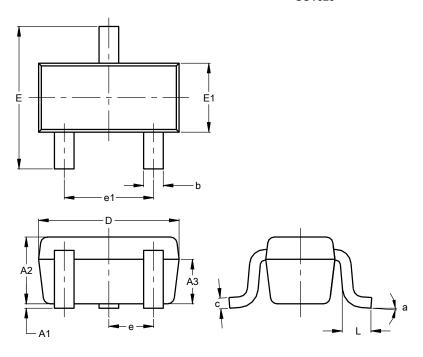




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

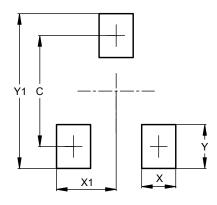


SOT523						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
A3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
С	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е	0.50 BSC					
e1	0.90	1.10	1.00			
L	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Y	0.51
Y1	1.80



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